

产品概览

NTTFS4H05N: 单 N 沟道功率 MOSFET 25V , 94A , 3.3mΩ

欲看完整文档，请参阅数据表。

功率 MOSFET 25V 94A 3.3 mΩ 单 N 沟道 μ8FL

特性

- Optimized Design to Minimize Conduction and Switching Losses
- Optimized Package to Minimize Parasitic Inductances
- Optimized material for improved thermal performance
- RoHS Compliant

应用

- High Performance DC-DC Conversion
- Point of Load
- System Voltage Rails

终端产品

- Netcom, Telecom
- Server

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(s)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (mΩ)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
NTTFS4H05NTAG	0.5637	Pb-free Halide free	Active	N-Channel	Single	25	20	2.1	94	46.3	-	4.8	3.8	16	8.7	1205	WDF N-8 / u8FL
NTTFS4H05NTWG	0.5637	Pb-free Halide free	Active	N-Channel	Single	25	20	2.1	94	46.3	-	4.8	3.8	16	8.7	1205	WDF N-8 / u8FL

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

创建于：7/15/2020